

isc Silicon NPN Power Transistor

2SD1173

DESCRIPTION

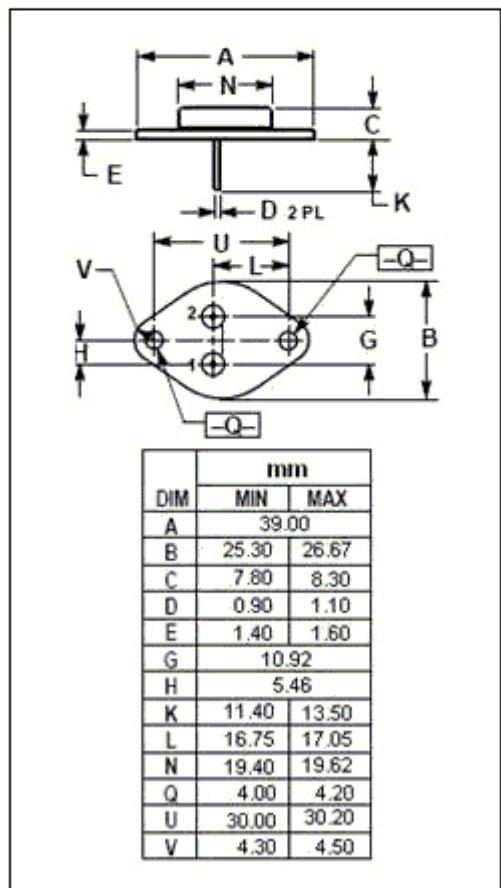
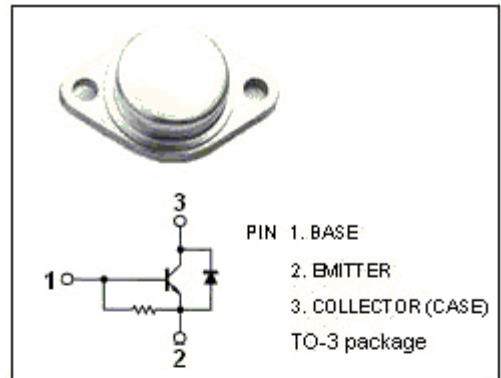
- High Breakdown Voltage-
: $V_{CBO} = 1500V$ (Min)
- High Power Dissipation
- Wide Area of Safe Operation

APPLICATIONS

- Designed for line-operated horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	4	A
I_{CP}	Collector Current-Pulse	6	A
P_C	Collector Power Dissipation @ $T_c T_c=25^\circ C$	70	W
T_J	Junction Temperature	130	$^\circ C$
T_{stg}	Storage Temperature Range	-65~130	$^\circ C$



isc Silicon NPN Power Transistor

2SD1173

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 500mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 1A			4.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3A; I _B = 1A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 750V ; I _E = 0			50	μ A
		V _{CB} = 1500V ; I _E = 0			1	mA
h _{FE}	DC Current Gain	I _C = 3A; V _{CE} = 10V	6		20	
V _{ECF}	C-E Diode Forward Voltage	I _F = 4A			2.5	V
t _f	Fall Time	I _C = 3A, I _{Bend} = 1A, L _B = 5 μ H			0.8	μ s
t _{stg}	Storage Time				10	μ s